

Form PTO-1449 INFORMATION DISCLOSURE CITATION OF AN APPLICATION (Use several sheets if necessary) JAN 09 2002 PATENT & TRADEMARK OFFICE	Docket Number (Optional) 2898.2US (88-070.7)	Application Number 09/776,387
	Applicant Protigal et al.	
	Filing Date February 2, 2001	Group Art Unit 2826

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
AS	3,699,722	10/1 972	Davidson et al.			
	4,061,999	12/1977	Proebsting et al.			
	4,271,461	06/1981	Hoffmann et al.			
	4,346,459	08/1982	Sud et al.			
	4,389,715	06/1983	Eaton, Jr. et al.			
	4,458,336	07/1984	Takemae			
	4,494,221	01/1985	Hardee et al.			
	4,566,081	01/1986	Ochii			
	4,587,639	05/1986	Aoyama et al.			
	4,628,214	12/1986	Leuschner			
	4,631,421	12/1986	Inoue et al.			
	4,658,379	04/1987	Fujishima et al.			

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO
AS	56-148859	11/1981	Japan			X	
	56-153778	11/1981	Japan			X	
	57-001902	01/1982	Japan			X	
	01-268032	10/1989	Japan			X (only)	

OTHER DOCUMENTS

(Including Author, Title, Date, Pertinent Pages, Etc.)

AS	McKenny, Verron D., "Good bits swapped for bad in 64-kilobit E-PROM," pps. 115-120 plus Cover and Table of Contents, <u>Electronics</u> , March 13, 1990.
AS	Natori et al., "FAM: 16.5: A 34ns 256K DRAM," pps. 232-233 plus Cover and Table of Contents, <u>IEEE International Solid-State Circuits Conference</u> , February 25, 1983.
	<u>Research Disclosure</u> , (3 pages), June 1985.
EXAMINER AS	DATE CONSIDERED 11-29-02

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.

Form PTO 1449

INFORMATION DISCLOSURE CITATION
IN AN APPLICATION

JAN 9 2002

(use several sheets if necessary)

Docket Number (Optional)
2898.2US (88-070.7)Application Number
09/776,387Applicant **Protigal et al.**Filing Date **February 2, 2001**Group Art Unit **2826**

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
A.S.	4,716,549	12/1987	Nakano et al.			
	4,730,276	03/1988	Waller			
	4,780,850	10/1988	Miyamoto et al.			
	4,780,851	10/1988	Kurakami			
	4,780,852	10/1988	Kajigaya et al.			
	4,829,480	05/1989	Seo			
	4,930,112	05/1990	Tanaka et al.			
	4,943,960	07/1990	Komatsu et al.			
	4,987,325	01/1991	Seo			
	5,012,132	04/1991	Wang			
	5,038,325	08/1991	Douglas et al.			
	5,042,011	08/1991	Casper et al.			

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO

OTHER DOCUMENTS

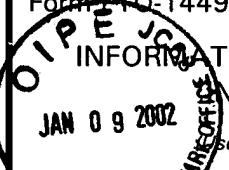
(Including Author, Title, Date, Pertinent Pages, Etc.)

A.S.		"Decoupling Capacitor Structure to Reduce FET Output Driver Switching Noise," pps. 167-168, <u>IBM Technical Disclosure Bulletin</u> , Vol 30., No. 7, December 1987.
A.S.		"MOS Memory," (4 pages), <u>Toshiba Mos Memory Products Data Book</u> , April 1987.
A.S.		"Double-Traversing Pseudo-Folded-Bitline Design for Cross-Point Memory Cells," pps. 246-248, <u>IBM Technical Disclosure Bulletin</u> , Vol. 30, No. 11, April 1988.

EXAMINER

DATE CONSIDERED

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U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
A.S.	5,177,908	01/1993	Tuttle			
	RE 34,425	11/1993	Schultz			
	5,315,551	05/1994	Hirayama			
	5,345,110	09/1994	Renfro et al.			
	RE 35,825	06/1998	Zager			

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO

OTHER DOCUMENTS

(Including Author, Title, Date, Pertinent Pages, Etc.)

A.S.		"New Memory Products 1987/1988," (4 pages), <u>NEC Electronics Inc. Supplement to 1986 Memory Products Data Book</u> , December 1987.
A.S.		Gillingham et al., "High-Speed, High-Reliability Circuit Design for Megabit DRAM," pps. 1171-1175 plus Table of Contents, <u>IEEE Journal of Solid-State Circuits</u> , Vol 26, No. 8, August 1991.
A.S.		"IBM's Response to Micron," (22 pages), December 8, 1995.

EXAMINER AS	DATE CONSIDERED 11.29.01
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